

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming a first insulating film, selected from a silicon oxide film, a silicon nitride film, and a silicon oxynitride film, on a semiconductor substrate;

~~forming a metal compound film directly or indirectly on a semiconductor substrate~~ on the first insulating film;

forming a ~~metal-containing~~ second insulating film comprising a metal oxide film or a metal silicate film by oxidizing said metal compound film; and

forming an electrode on said ~~metal-containing~~ second insulating film;

~~wherein an insulating film selected from a silicon oxide film, a silicon nitride film and a silicon oxynitride film is interposed between said semiconductor substrate and said metal compound film before forming said metal-containing insulating film by oxidizing said metal compound film.~~
2. (Canceled)
3. (Original) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film has a thickness not larger than 5 nm.

4. (Currently Amended) The method of manufacturing a semiconductor device according to claim 1, wherein formation of said metal compound film and formation of said ~~metal-containing~~ second insulating film by oxidation of the metal compound film are repeated a plurality of times.
5. (Canceled)
6. (Previously Presented) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film is selected from a metal nitride film, an oxygen-containing metal nitride film, a silicon-containing metal nitride film, a metal nitride film containing both oxygen and silicon, a metal carbide film, an oxygen-containing metal carbide film, a silicon-containing metal carbide film, a metal carbide film containing both oxygen and silicon, a metal carbonitride film, an oxygen-containing metal carbonitride film, a silicon-containing metal carbonitride film, and a metal carbonitride film containing both oxygen and silicon.
7. (Previously Presented) The method of manufacturing a semiconductor device according to claim 1, wherein said metal compound film contains at least one metal selected from titanium, zirconium, hafnium, tantalum, niobium, aluminum, yttrium and cerium.

8. (Previously Presented) A method of manufacturing a semiconductor device comprising:
 - forming a metal compound film directly or indirectly on a semiconductor substrate;
 - forming a metal-containing insulating film comprising a metal oxide film or a metal silicate film by oxidizing said metal compound film; and
 - forming an electrode on said metal-containing insulating film,wherein said metal-containing insulating film comprises a plurality of first insulating regions formed of grains containing a metal oxide of a metal element contained in said metal compound film and a second insulating region formed of an amorphous insulating material, and each of said first insulating regions is formed in said second insulating region.
9. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains a metal element forming said metal oxide and silicon, said first insulating region contains a crystal of said metal oxide, and said second insulating region contains silicon, oxygen and a metal element forming said metal oxide.
10. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains a first metal element forming said metal oxide and a second metal element differing from said first metal

element, said first insulating region contains a crystal of said metal oxide, and said second insulating region contains oxygen and said second metal element.

11. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains a metal element forming said metal oxide, said first insulating region is formed of crystal grains of said metal oxide, and said second insulating region is formed of an amorphous region of said metal oxide.

12-20. (Canceled)

21. (Previously Presented) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film has a thickness not larger than 5 nm.
22. (Previously Presented) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film is selected from a metal nitride film, an oxygen-containing metal nitride film, a silicon-containing metal nitride film, a metal nitride film containing both oxygen and silicon, a metal carbide film, an oxygen-containing metal carbide film, a silicon-containing metal carbide film, a metal carbide film containing both oxygen and silicon, a metal carbonitride film, an oxygen-containing metal carbonitride film, a silicon-

containing metal carbonitride film, and a metal carbonitride film containing both oxygen and silicon.

23. (Previously Presented) The method of manufacturing a semiconductor device according to claim 8, wherein said metal compound film contains at least one metal selected from titanium, zirconium, hafnium, tantalum, niobium, aluminum, yttrium, and cerium.